

QIAOXIN N-Channel Enhancement Mode Power MOSFET

Description

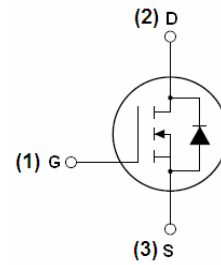
The VCRR01H10D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

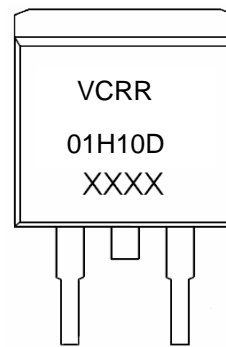
- $V_{DS} = 100V, I_D = 100A$
 $R_{DS(ON)} < 13m\Omega @ V_{GS}=10V$ (Typ:9.9m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin assignment



TO-263-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VCRR01H10D	VCRR01H10D	TO-263-2L	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	100	A
$I_D(100^\circ C)$	Drain Current-Continuous($T_C=100^\circ C$)	80	A
I_{DM}	Pulsed Drain Current	380	A
P_D	Maximum Power Dissipation	200	W
	Derating factor	1.33	W/ $^\circ C$
E_{AS}	Single pulse avalanche energy (Note 5)	800	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	$^\circ C$

Thermal Characteristic

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 2)	0.75	$^{\circ}\text{C}/\text{W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

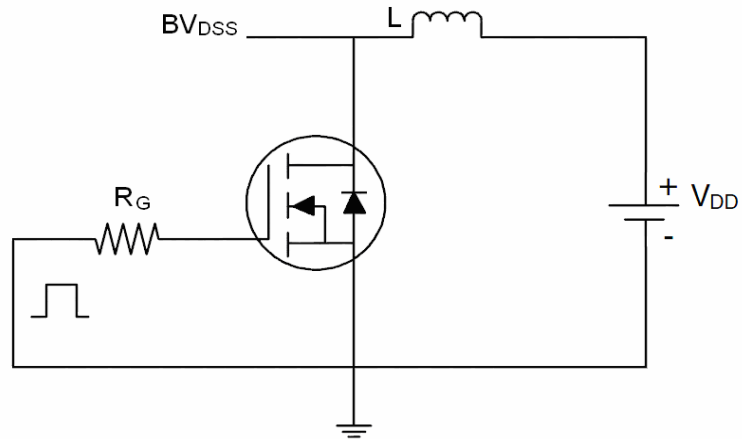
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	110	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=40A$	-	9.9	13	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=10V, I_D=20A$	50	-	-	S
Dynamic Characteristics (Note 4)						
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	4800	-	PF
C_{oss}	Output Capacitance		-	340	-	PF
C_{rss}	Reverse Transfer Capacitance		-	150	-	PF
Switching Characteristics (Note 4)						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=50V, I_D=40A$ $V_{GS}=10V, R_{GEN}=2.5\Omega$	-	15	-	nS
t_r	Turn-on Rise Time		-	50	-	nS
$t_{d(off)}$	Turn-Off Delay Time		-	40	-	nS
t_f	Turn-Off Fall Time		-	55	-	nS
Q_g	Total Gate Charge	$V_{DS}=80V, I_D=40A,$ $V_{GS}=10V$	-	85	-	nC
Q_{gs}	Gate-Source Charge		-	18	-	nC
Q_{gd}	Gate-Drain Charge		-	28	-	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage (Note 3)	$V_{GS}=0V, I_S=40A$	-	-	1.2	V
I_S	Diode Forward Current (Note 2)	-	-	-	57	A
t_{rr}	Reverse Recovery Time	$T_J = 25^{\circ}\text{C}, I_F = 40A$	-	38	80	nS
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s(\text{Note}3)$	-	53	100	nC
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

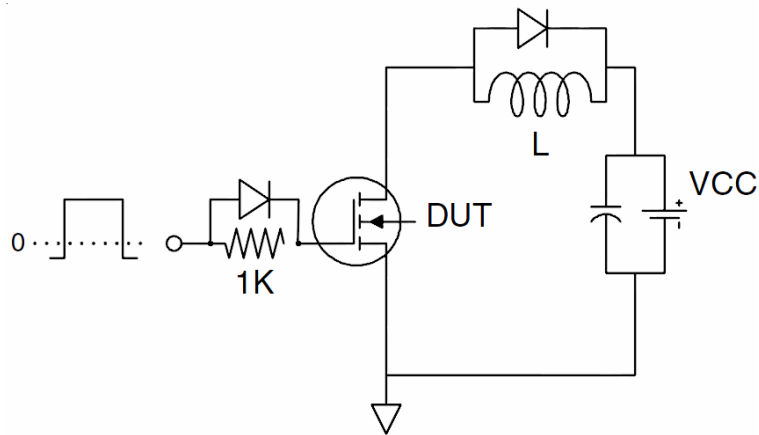
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit

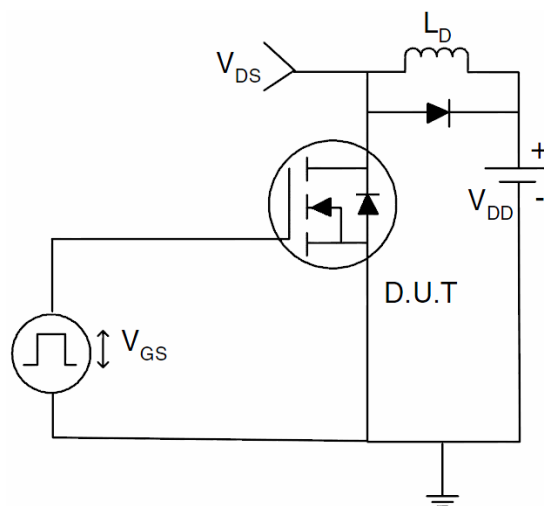
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

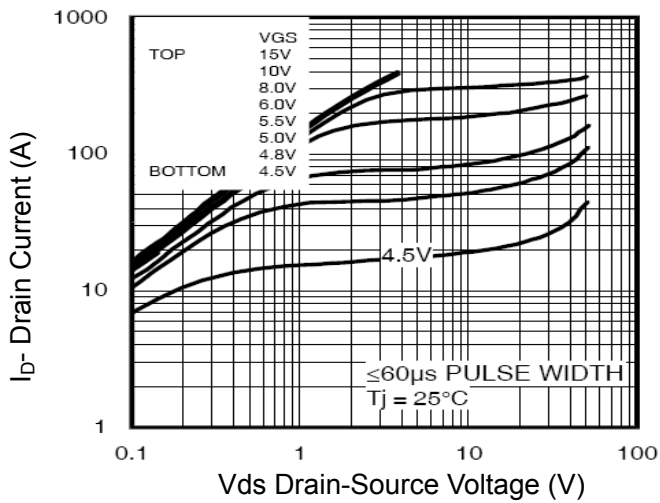


Figure 1 Output Characteristics

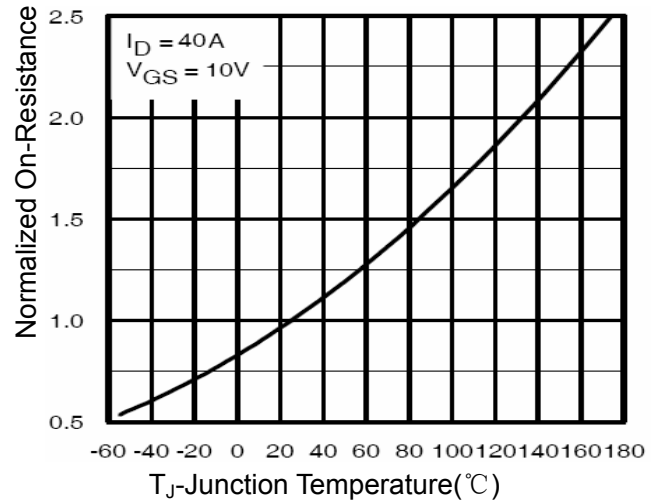


Figure 4 Rdson-Junction Temperature

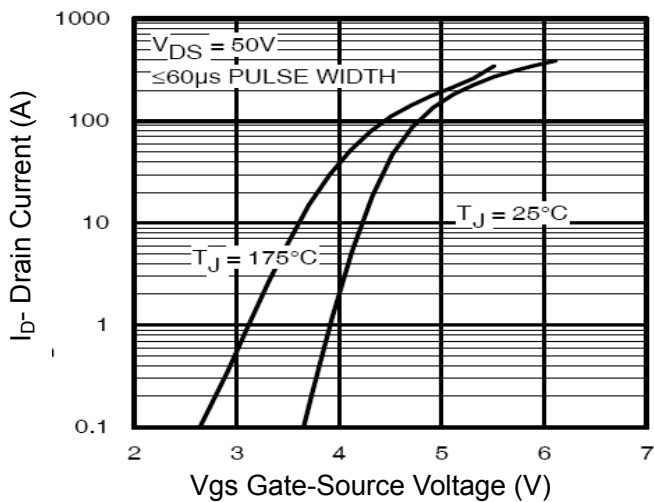


Figure 2 Transfer Characteristics

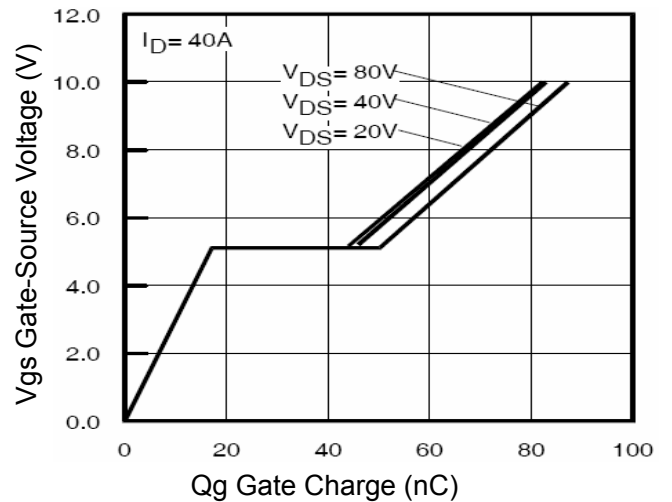


Figure 5 Gate Charge

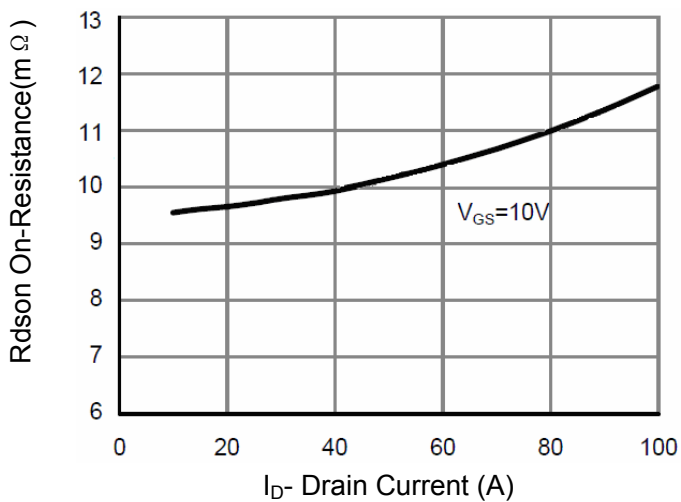


Figure 3 Rdson- Drain Current

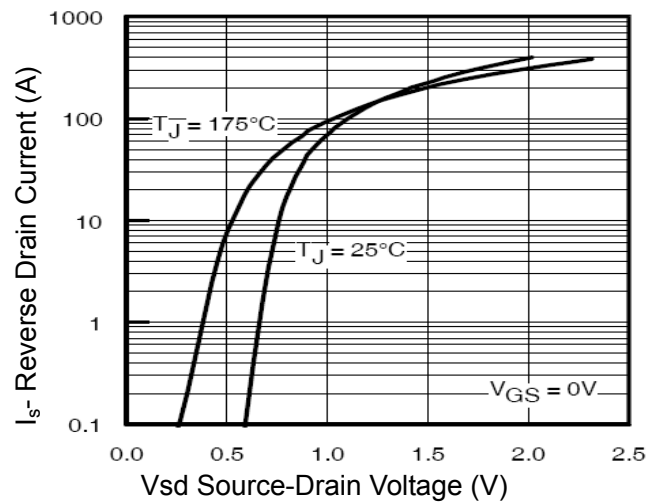


Figure 6 Source- Drain Diode Forward

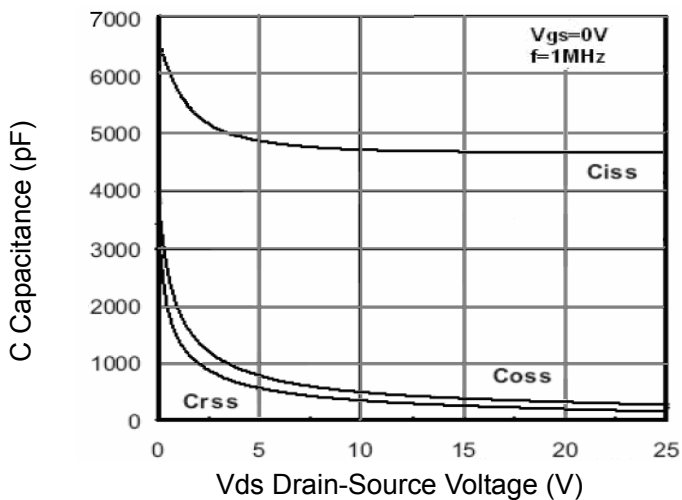


Figure 7 Capacitance vs Vds

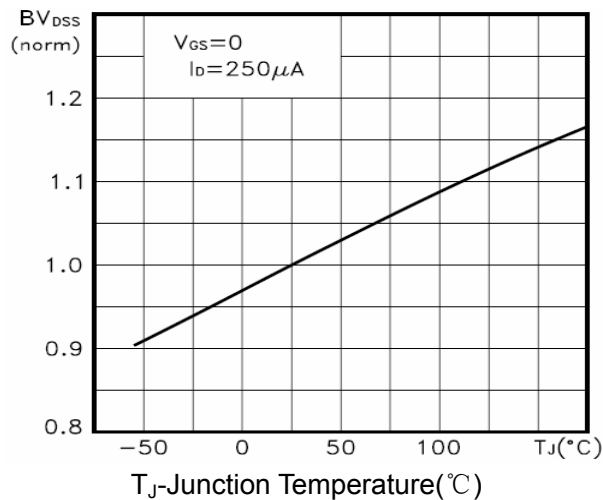


Figure 9 BV_{DSS} vs Junction Temperature

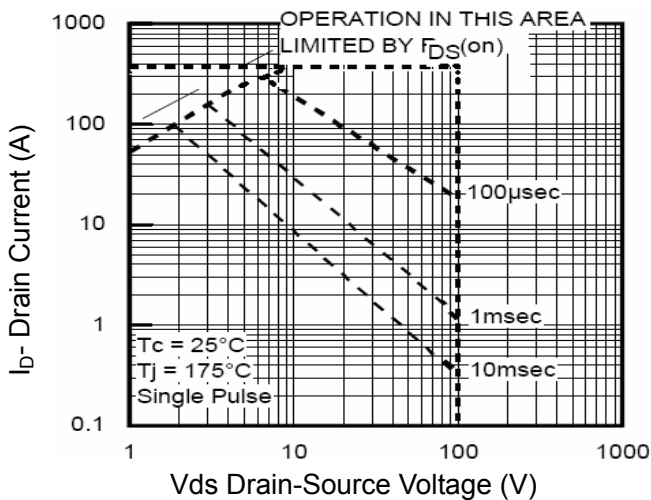


Figure 8 Safe Operation Area

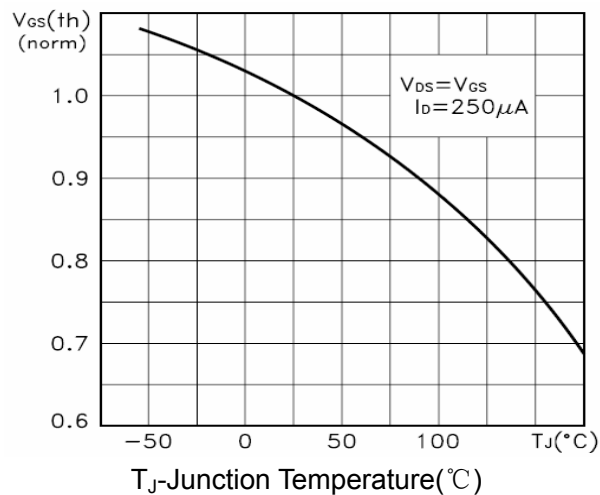


Figure 10 V_{GS(th)} vs Junction Temperature

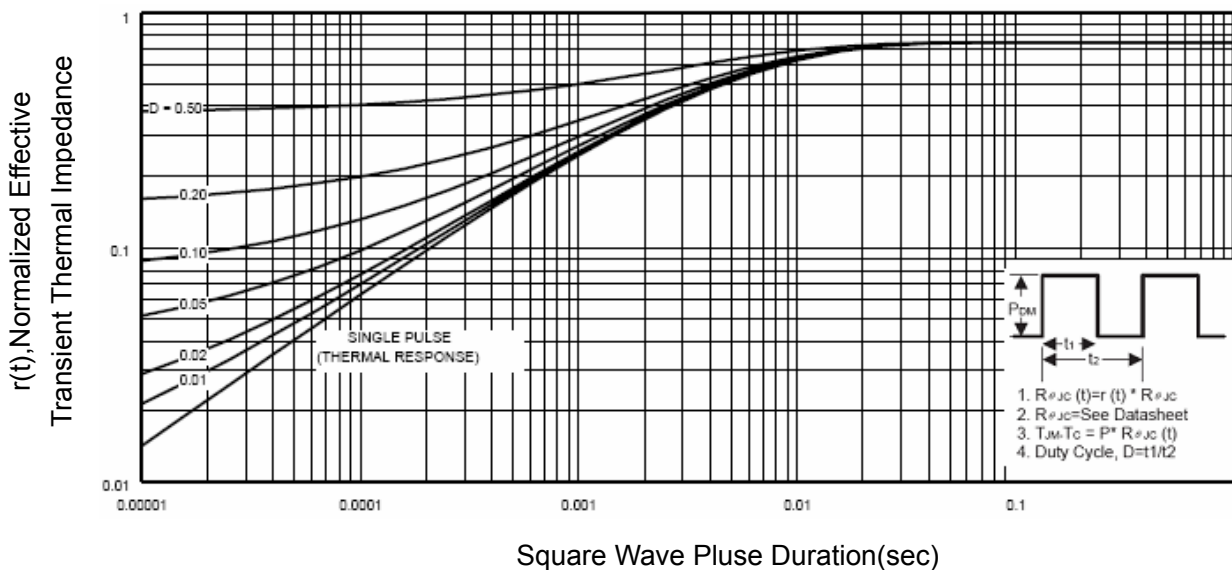
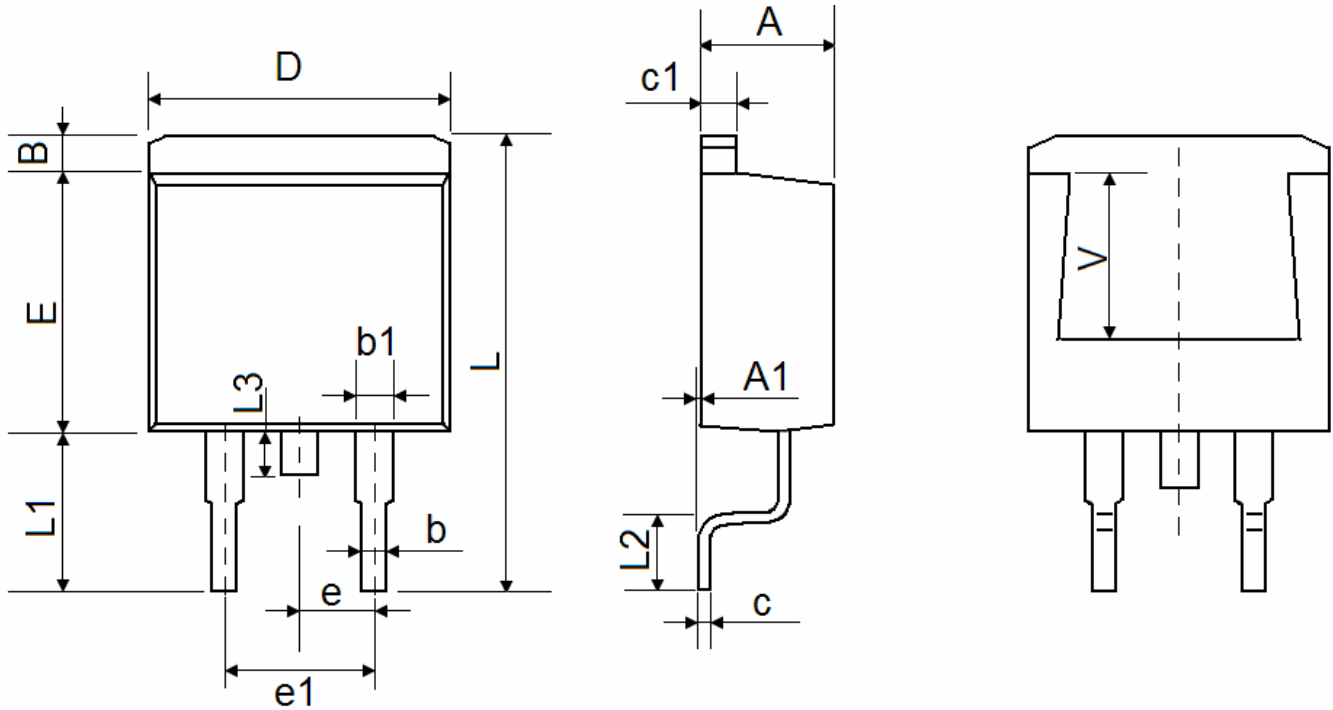


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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